

## **IN THE SPECIFICATION**

**Please rewrite the paragraph on page 8, lines 13-26, as follows:**

A P-type epitaxial layer 3 is formed on the entire surface of the P-type bulk substrate 2. The P-type epitaxial layer 3 is formed by performing epitaxial growth onto a P-type silicon layer with a CVD method (Chemical Vapor Deposition method) using source gas of silane series. The thickness of the P-type epitaxial layer 3 is 5 $\mu$ m, for example, and the resistivity is approximately equal to the resistivity of the conventional semiconductor substrate, which is 10 $\Omega$ ·cm for example. The impurity concentration of the P-type bulk substrate 2 is one hundredth or less than the impurity concentration of the P-type epitaxial layer 3, for example. The P-type bulk substrate 2 and the P-type epitaxial layer 3 essentially ~~consist~~ comprise the semiconductor substrate 4 according to this embodiment.

**Please rewrite the paragraphs on page 9, lines 11-15, as follows:**

The reason for limiting the numerical values in the ~~constituent~~ constituents of the present invention will be described as follows.

The resistivity of the support substrate: 20 substrate is 20 times or more the resistivity of the semiconductor layer

**Please rewrite the paragraphs beginning on page 10, line 23, and ending on page 11, line 17, as follows:**

In addition, since the device isolation region 7 reaching the P-type bulk substrate 2 is provided in the region between the digital section 5 and analog section 6 of the P-type epitaxial layer 3, the digital section 5 and analog section 6 are electrically isolated from each other. For

this reason, the noise 8 is inhibited to ~~propagate~~ from propagating in the P-type epitaxial layer 3 as well.

In this embodiment, as described, setting the P-type bulk substrate 2 to the high resistance inhibits the noise to ~~propagate~~ from propagating between the digital section 5 and analog section 6. Further, since the P-type epitaxial layer 3 has the resistivity equal to that of the conventional semiconductor substrate, process conditions such as the ion implantation conditions and the well concentration can be set to the same conditions as the conventional process conditions when manufacturing the digital circuit and analog circuit. Thus, it is not necessary to change a conventional device platform, and there is no need to develop new process conditions, or develop and adjust a production line in order to manufacture the semiconductor integrated circuit 1. Therefore, time for the development and adjustment is not needed, and the semiconductor integrated circuit 1 can be manufactured at a low cost and in short time.

**Please rewrite the paragraph on page 12, lines 11-26, as follows:**

In the following, the effects of the present invention will be specifically described in comparison with a comparative example that departs from the scope of what is claimed by the invention. Fig. 4 is the graph showing the effect that the resistivity of the support substrate causes to the noise propagation by ~~taking~~ placing the resistivity of support substrate on the ~~axis of abscissas~~ abscissa and propagation characteristic of the noise in the support substrate on the ~~axis of ordinates~~ ordinate. A plurality of the semiconductor integrated circuits as shown in the above-described embodiment were manufactured. At this point, the resistivity of the P-type bulk substrates were made different from each other among the plurality of semiconductor integrated

circuits, and the ~~affect~~ effect that the resistivity of the support substrate causes to the noise propagation ~~were~~ was inspected.

**Please rewrite the paragraph on page 13, lines 7-17, as follows:**

As shown in Fig. 4, the noise propagation quantity between the P-type diffusion layers ~~reduced~~ decreased as the resistivity of the P-type bulk substrate as the support substrate ~~became~~ higher. increased. Practically, the noise propagation characteristic is -40dB (1/100) or less, preferably. Consequently, as shown in Fig. 4, in the case where the resistivity of the P-type epitaxial layer is  $10\Omega\cdot\text{cm}$ , the noise propagation characteristic is -60dB when the resistivity of the P-type bulk substrate (support substrate) is  $1000\Omega\cdot\text{cm}$ , and thus the noise propagation is inhibited to a practically sufficient level.